



# BUK9Y8R7-60E

N-channel 60 V, 8.7 mΩ logic level MOSFET in LFPAK56

8 May 2013

Product data sheet

## 1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)}$  rating of greater than 0.5 V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	60	V
$I_D$	drain current	$V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	86	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	-	147	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$ ; $I_D = 20\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	6.8	8.7	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 5\text{ V}$ ; $I_D = 20\text{ A}$ ; $V_{DS} = 48\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>	-	9.7	-	nC

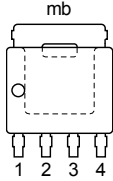
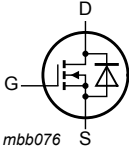


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## 5. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p><b>LPAK56; Power-SO8 (SOT669)</b></p>	 <p><i>mbb076</i></p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BUK9Y8R7-60E	LPAK56; Power-SO8	Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

**Table 4. Marking codes**

Type number	Marking code
BUK9Y8R7-60E	98E760

## 8. Limiting values

**Table 5. Limiting values**

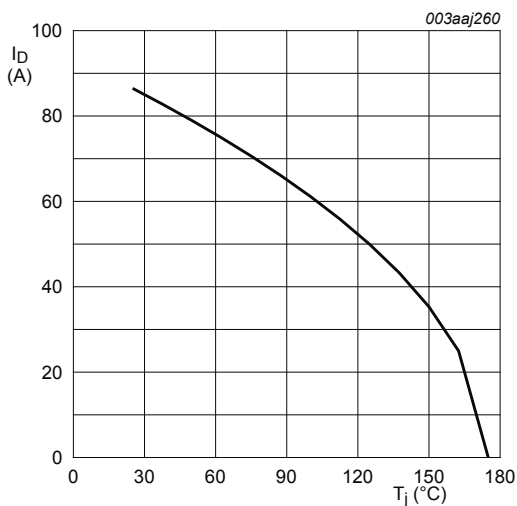
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	60	V
$V_{GS}$	gate-source voltage	$T_j \leq 175\text{ °C}; \text{DC}$	-10	10	V
		$T_j \leq 175\text{ °C}; \text{Pulsed}$	[1][2]	15	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 5\text{ V}; \text{Fig. 1}$	-	86	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 5\text{ V}; \text{Fig. 1}$	-	61	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}; \text{pulsed}; t_p \leq 10\text{ }\mu\text{s}; \text{Fig. 4}$	-	346	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$	-	147	W

N-channel 60 V, 8.7 mΩ logic level MOSFET in LPAK56

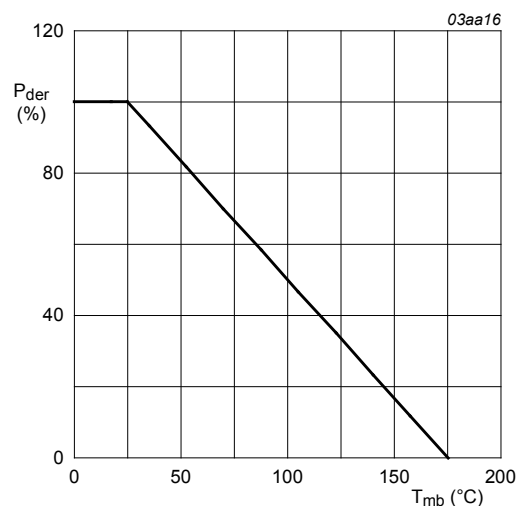
Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	86	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	346	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 86 A; V <sub>sup</sub> ≤ 60 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped; <a href="#">Fig. 3</a>	[3][4]	-	76.5 mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T<sub>j</sub> and or V<sub>GS</sub>
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.



**Fig. 1. Continuous drain current as a function of mounting base temperature**

$$V_{GS} \geq 5V$$



**Fig. 2. Normalized total power dissipation as a function of mounting base temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

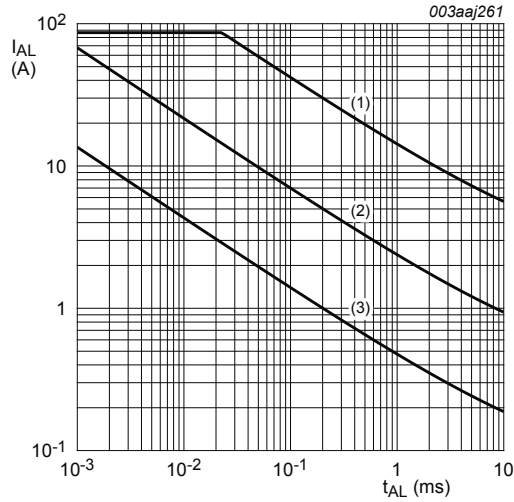


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j (int)} = 25^{\circ}C$ ; (2)  $T_{j (int)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

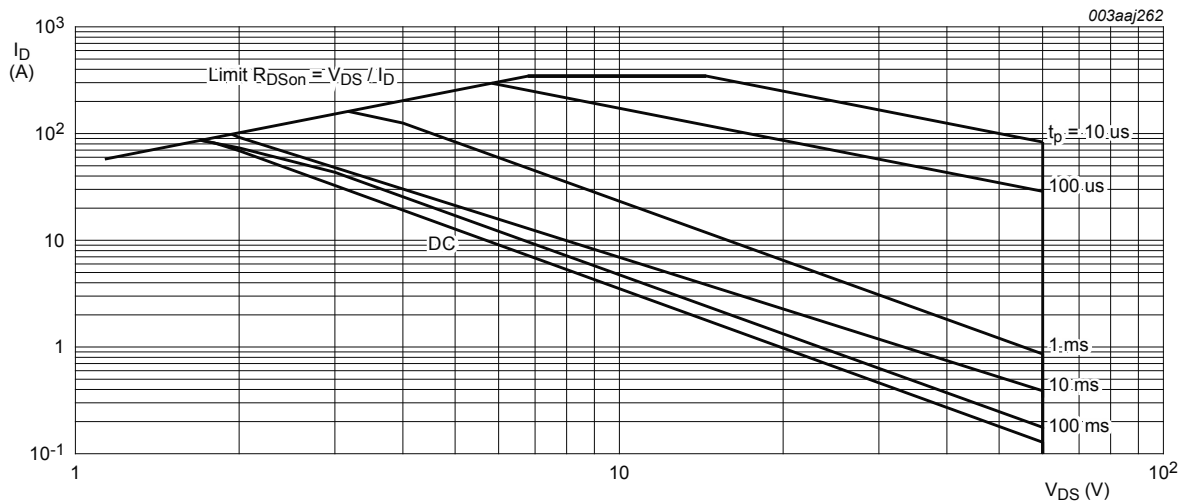


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>	-	-	1.02	K/W

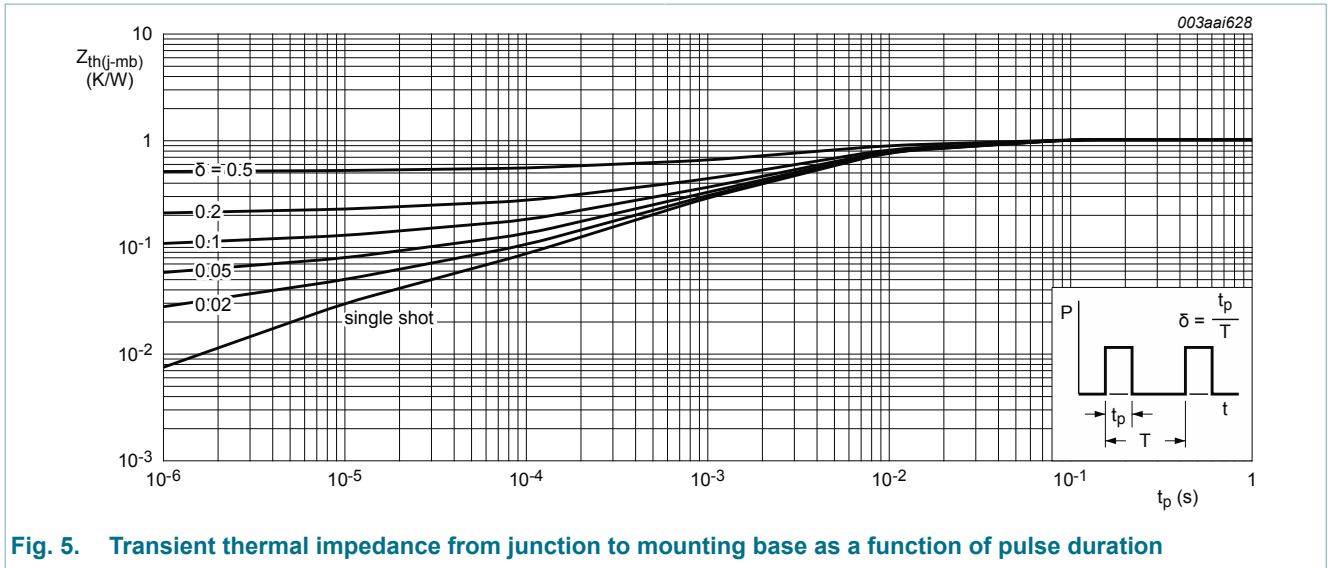


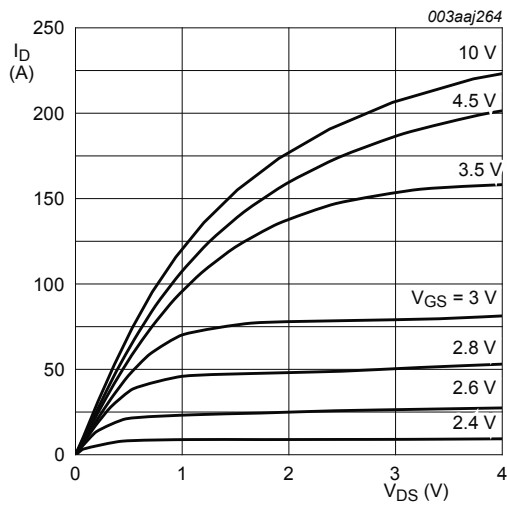
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

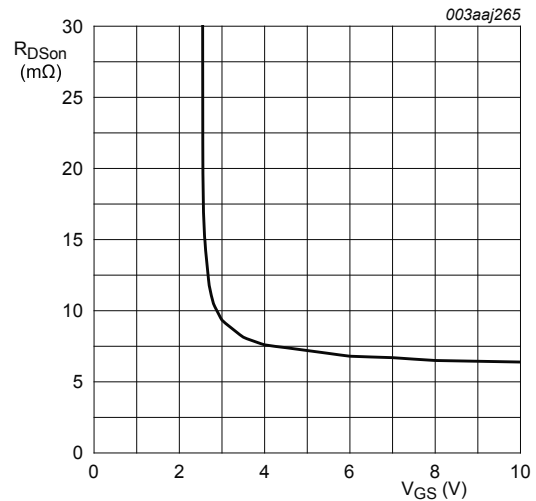
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	60	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 9; Fig. 10</a>	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$ <a href="#">Fig. 9</a>	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 9</a>	0.5	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.05	10	$\mu A$
		$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5 V; I_D = 20 A; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	6.8	8.7	mΩ
		$V_{GS} = 10 V; I_D = 20 A; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	6	7.5	mΩ
		$V_{GS} = 5 V; I_D = 20 A; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 12; Fig. 11</a>	-	-	19.7	mΩ
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 20 A; V_{DS} = 48 V; V_{GS} = 5 V;$ $T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 13; Fig. 14</a>	-	31	-	nC
$Q_{GS}$	gate-source charge		-	9	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{GD}$	gate-drain charge		-	9.7	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz};$	-	3435	4570	pF
$C_{oss}$	output capacitance	$T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>	-	295	355	pF
$C_{rss}$	reverse transfer capacitance		-	150	205	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 45\text{ V}; R_L = 2\text{ } \Omega; V_{GS} = 5\text{ V};$	-	17	-	ns
$t_r$	rise time	$R_{G(ext)} = 5\text{ } \Omega; T_j = 25\text{ }^\circ\text{C}$	-	30	-	ns
$t_{d(off)}$	turn-off delay time		-	42	-	ns
$t_f$	fall time		-	26	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 20\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 16</a>	-	0.82	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	24	-	ns
$Q_r$	recovered charge	$V_{DS} = 25\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	22.3	-	nC



$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ } \mu\text{s}$

**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25\text{ }^\circ\text{C}; I_D = 20\text{ A}$

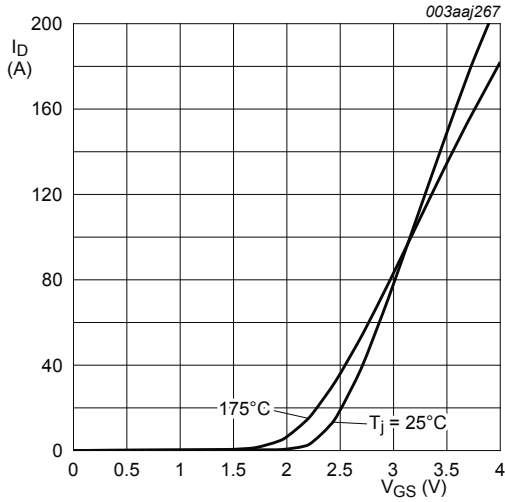


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

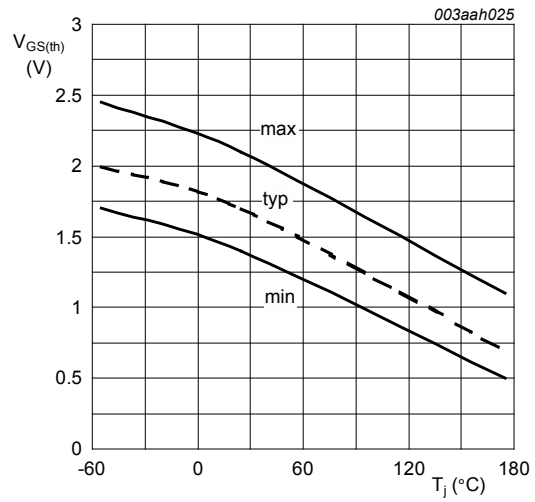


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

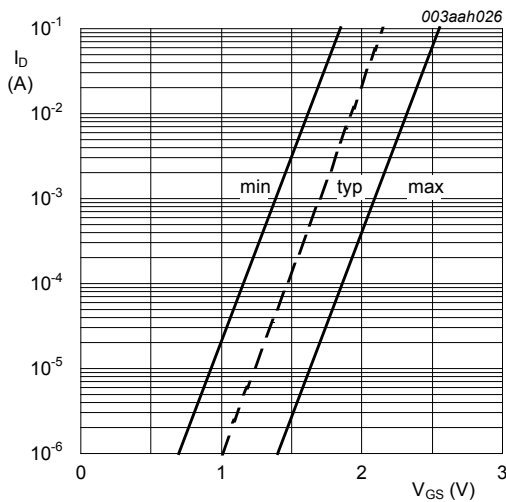


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = 5V$

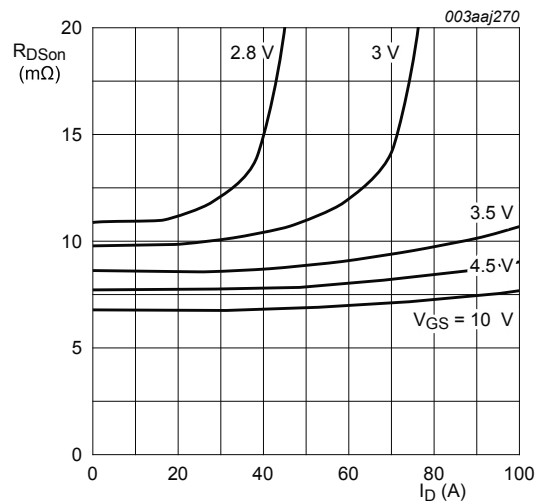
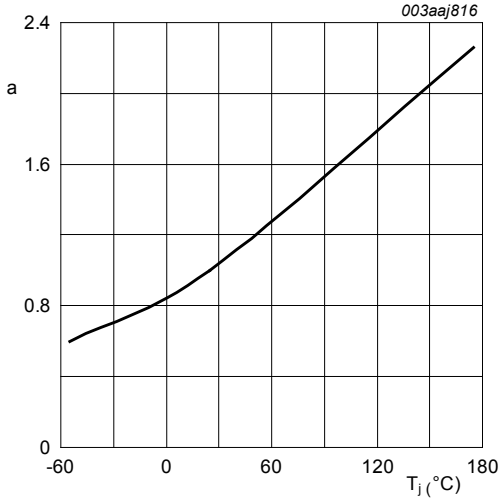


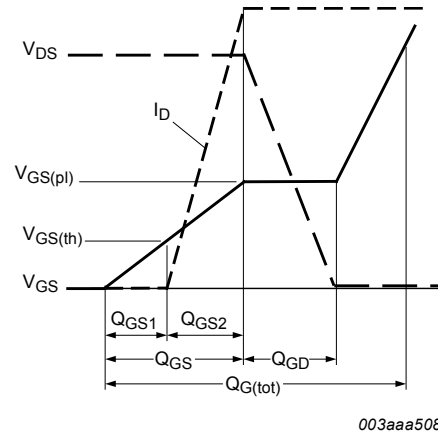
Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; t_p = 300 \mu\text{s}$

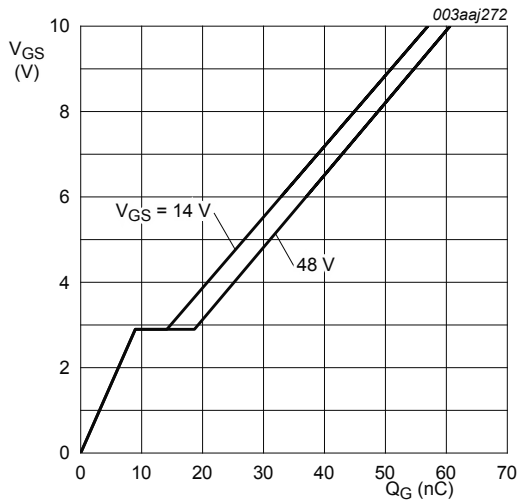


**Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^{\circ}\text{C})}$$

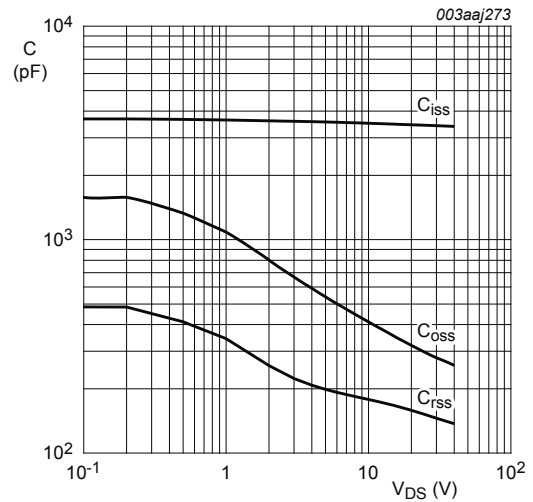


**Fig. 13. Gate charge waveform definitions**



**Fig. 14. Gate-source voltage as a function of gate charge; typical values**

$$T_j = 25^{\circ}\text{C}; I_D = 20\text{A}$$



**Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

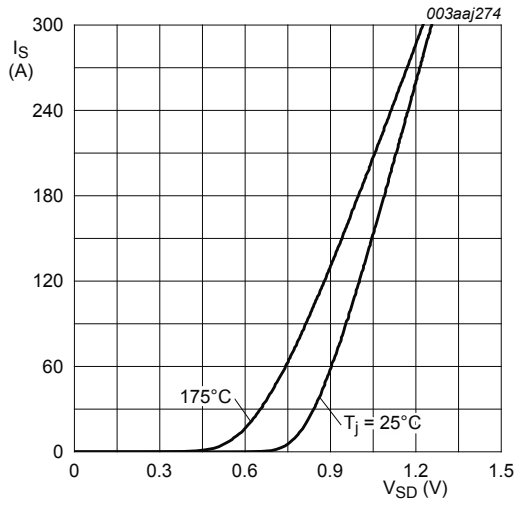
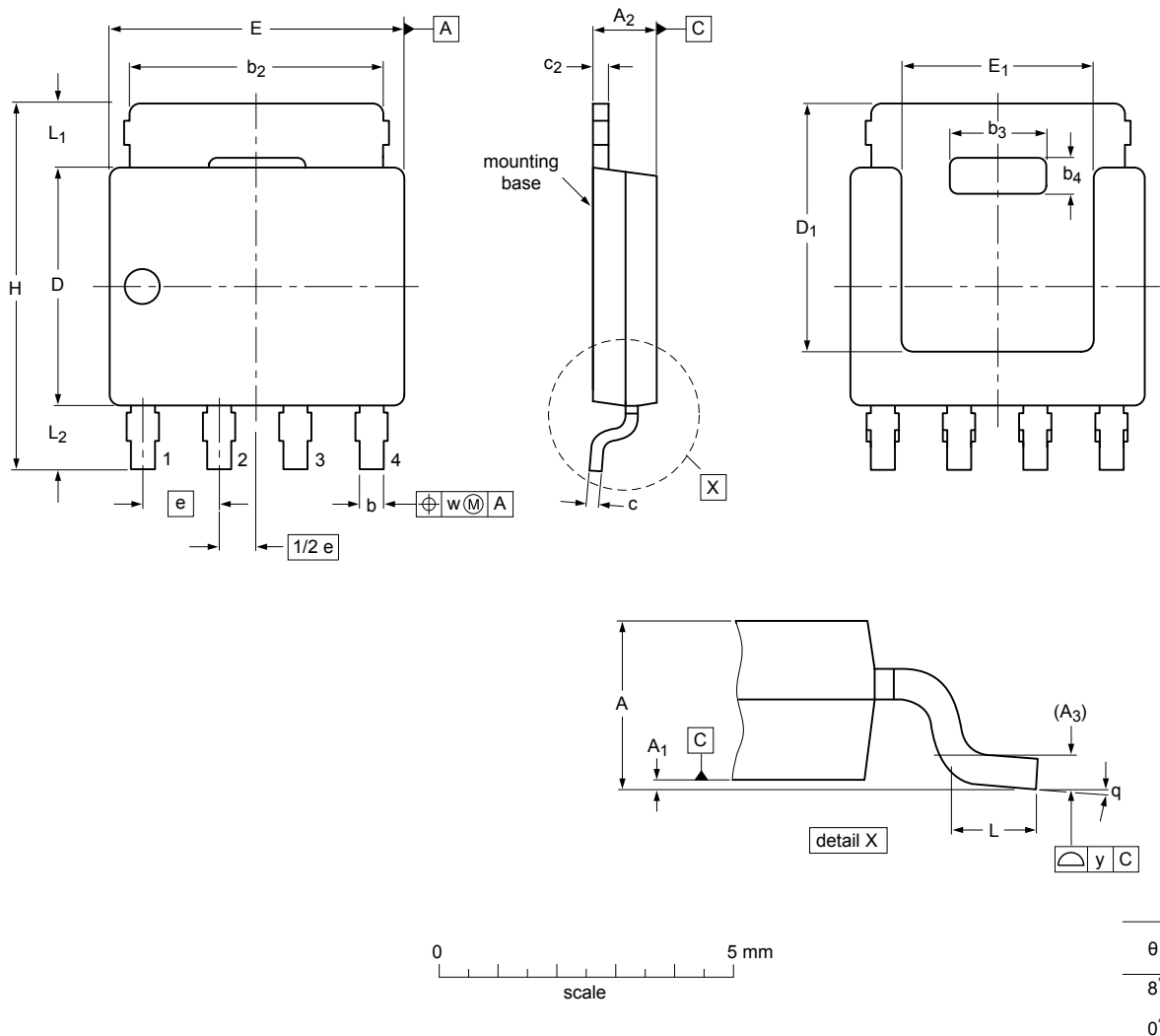


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

**11. Package outline**

Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads SOT669



Dimensions (mm are the original dimensions)

Unit <sup>(1)</sup>	A	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b	b <sub>2</sub>	b <sub>3</sub>	b <sub>4</sub>	c	c <sub>2</sub>	D <sup>(1)</sup>	D <sub>1</sub> <sup>(1)</sup>	E <sup>(1)</sup>	E <sub>1</sub> <sup>(1)</sup>	e	H	L	L <sub>1</sub>	L <sub>2</sub>	w	y
max	1.20	0.15	1.10		0.50	4.41	2.2	0.9	0.25	0.30	4.10	4.20	5.0	3.3	1.27	6.2	0.85	1.3	1.3		
nom				0.25																0.25	0.1
min	1.01	0.00	0.95		0.35	3.62	2.0	0.7	0.19	0.24	3.80		4.8	3.1		5.8	0.40	0.8	0.8		

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

sot669\_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT669		MO-235				-11-03-25- 13-02-27

**Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)**

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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